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C mplete if Kn wn **Application Number** TBA **INFORMATION DISCLOSURE Filing Date** Herewith First Named Invent r Christopher B. Kocon STATEMENT BY APPLICANT **Group Art Unit** (use as many sheets as nec ssary) **Examiner Name** E. Ortiz (Recommended) 90065.146801 Attorney Docket Number

				U.S. PATENT DOC	UMENTS	
Examiner Initials*	Cite No.1	U.S. Paten Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No.1	Office ³	Number ⁴	Kind Code ⁵ (if known)			Passages or Relevant Figures Appear	T ⁶
TAX	*13	JP	02144971		Hitachi, Ltd.	04/06/1990		<u> </u>
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Date Examiner Considered Signature

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁸ Applicant is to place a check mark here if English language Translation is attached.

Signature



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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C mpl te if Kn wn				
Application Number	TBA			
Filing Date	Herewith			
First Named Inventor	Christopher B. Kocon			
Group Art Unit	2815			
Examiner Name	E. Ortiz (Recommended)			
Attorney Docket Number	90065.146801			

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	_
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Т
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